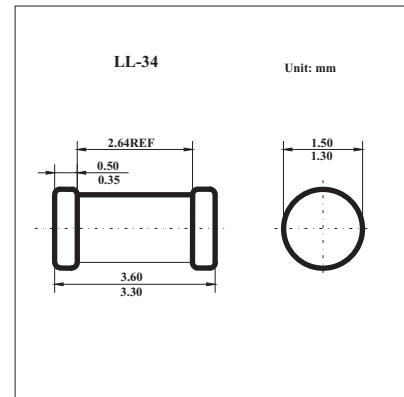


Schottky Barrier Diode

KAS85(BAS85)

■ Features

- Low forward voltage
- High breakdown voltage
- Guard ring protected



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---|---------------|-------------|------------------|
| continuous reverse voltage | V_R | 30 | V |
| continuous forward current | I_F | 200 | mA |
| average forward current ($V_{RWM} = 25\text{ V}$; $a = 1.57$; $\delta = 0.5$) | $I_{F(AV)}$ | 200 | mA |
| repetitive peak forward current ($t_p \leq 1\text{ s}$; $\delta \leq 0.5$) | I_{FRM} | 300 | mA |
| non-repetitive peak forward current ($t_p = 10\text{ ms}$) | I_{FSM} | 5 | A |
| thermal resistance from junction to ambient | $R_{th\ j-a}$ | 320 | K/W |
| operating ambient temperature | T_{amb} | -65 to +125 | $^\circ\text{C}$ |
| junction temperature | T_j | 125 | $^\circ\text{C}$ |
| storage temperature | T_{stg} | -65 to +150 | $^\circ\text{C}$ |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Testconditions | Max | Unit |
|-------------------|--------|---|-----|----------------|
| forward voltage | V_F | $I_F = 0.1\text{ mA}$ | 240 | mV |
| | | $I_F = 1\text{ mA}$ | 320 | |
| | | $I_F = 10\text{ mA}$ | 400 | |
| | | $I_F = 30\text{ mA}$ | 500 | |
| | | $I_F = 100\text{ mA}$ | 800 | |
| reverse current | I_R | $V_R = 25\text{ V}^*$ | 2.3 | $\mu\text{ A}$ |
| diode capacitance | C_d | $f = 1\text{ MHz}$; $V_R = 1\text{ V}$ | 10 | pF |

* Pulsed test: $t_p = 300\ \mu\text{s}$; $\delta = 0.02$.